Panasonic 1 Process Variations for CHF₃-Based SiO₂ etching

Based on Recipe 118, SiOVert, CHF₃ flow = 40sccm

**Oxide Etch Rate vs Pressure**

![Graph showing oxide etch rate vs pressure for different power settings.](image)
Based on Recipe 118, SiOVert, CHF$_3$ flow = 40sccm

Oxide:Resist Etch Ratio vs Pressure
Based on Recipe 118, SiOVert, CHF$_3$ flow = 40sccm

ICP/Bias/Pressure